Octal 3-State Noninverting D Flip-Flop with LSTTL-Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT374A may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs.

The HCT374A is identical in pinout to the LS374.

Data meeting the setup and hold time is clocked to the outputs with the rising edge of Clock. The Output Enable does not affect the state of the flip-flops, but when Output Enable is high, the outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HCT374A is identical in function to the HCT574A, which has the input pins on the opposite side of the package from the output pins. This device is similar in function to the HCT534A, which has inverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance With the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 276 FETs or 69 Equivalent Gates
- Improvements over HCT374
 - Improved Propagation Delays
 - 50% Lower Quiescent Power
 - Improved Input Noise and Latchup Immunity
- Pb-Free Packages are Available*



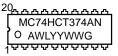
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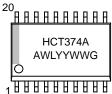
MARKING DIAGRAMS



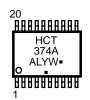
PDIP-20 N SUFFIX CASE 738













SOEIAJ-20 F SUFFIX CASE 967



A = Assembly Location

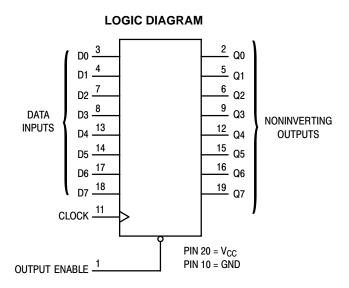
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



Design Criteria	Value	Units
Internal Gate Count*	69	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рJ

^{*}Equivalent to a two-input NAND gate.

PIN ASSIGNMENT OUTPUT ENABLE 20 | V_{CC} 19 Q7 Q0 [2 D0 🛮 3 18 D7 17 D6 D1 [] 4 Q1 [16 🛮 Q6 15 Q5 Q2 [6 D2 [7 14 D5 13 D4 D3 🛮 8 12 Q4 Q3 🛮 9 11 CLOCK GND [10

FUNCTION TABLE

Inputs			Output
Output Enable	Clock	D	Q
L		Н	Н
L		L	L.
L.	L,H,⁻∕₋	Х	No Change
Н	X	Х	Z

X = don't careZ = high impedance

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT374AN	PDIP-20	1440 Units / Box
MC74HCT374ANG	PDIP-20 (Pb-Free)	1440 Units / Box
MC74HCT374ADW	SOIC-20	38 Units / Rail
MC74HCT374ADWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74HCT374ADWR2	SOIC-20	1000 Units / Reel
MC74HCT374ADWR2G	SOIC-20 (Pb-Free)	1000 Units / Reel
MC74HCT374ADTR2	TSSOP-20*	2500 Units / Reel
MC74HCT374ADTR2G	TSSOP-20*	2500 Units / Reel
MC74HCT374AFEL	SOEIAJ-20	2000 Units / Reel
MC74HCT374AFELG	SOEIAJ-20 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed L	imit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
I _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ
I _{OZ}	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	5.5	± 0.5	± 5.0	± 10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ
ΔI_{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input		≥ -55 °(25°0	C to 125°C	
		$V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0 \mu A$	5.5	2.9		2.4	mA

^{1.} Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D)

AC ELECTRICAL CHARACTERISTICS (V_{CC} = $5.0 \text{ V} \pm 10\%$, C_L = 50 pF, Input t_r = t_f = 6.0 ns)

		Gua	ranteed Limi	it	
Symbol	Parameter	− 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	30	24	20	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	31	39	47	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	30	38	45	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	30	38	45	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	12	15	18	ns
C _{in}	Maximum Input Capacitance	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)	15	15	15	pF

For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D)

		Typical @ 25°C, V _{CC} = 5.0 V		Ī
C_{PD}	Power Dissipation Capacitance (Per Flip-Flop)*	65	pF	

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (V_{CC} = 5.0 V \pm 10%, Input t_r = t_f = 6.0 ns)

		Guaranteed Limit			
Symbol	Parameter	– 55 to 25°C	≤ 85 ° C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, Data to Clock (Figure 3)	12	15	18	ns
t _h	Minimum Hold Time, Clock to Data (Figure 3)	5.0	5.0	5.0	ns
t _w	Minimum Pulse Width, Clock (Figure 1)	12	15	18	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	500	500	500	ns

SWITCHING WAVEFORMS

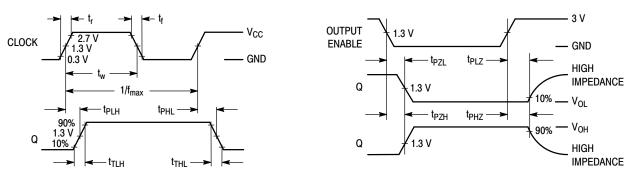


Figure 1.

Figure 2.

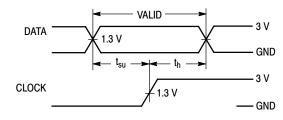
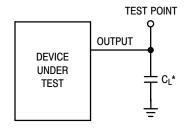
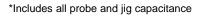
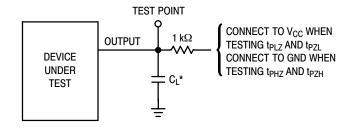


Figure 3.

TEST CIRCUITS





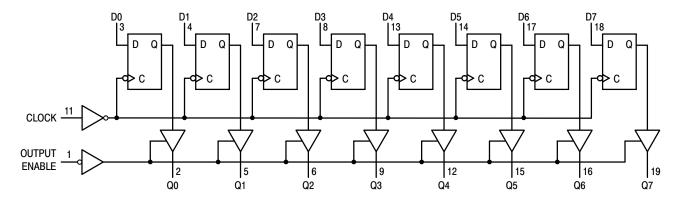


*Includes all probe and jig capacitance

Figure 4.

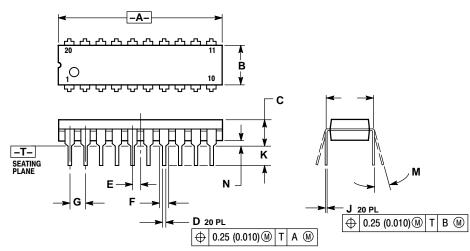
Figure 5.

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** CASE 738-03 **ISSUE E**

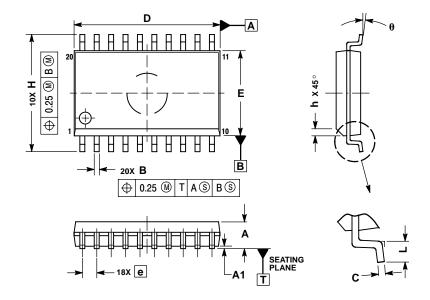


NOTES:

- IOLES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN
 FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD
- FLASH.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
Е	0.050	BSC	1.27 BSC		
F	0.050	0.070	1.27	1.77	
G	0.100	.100 BSC 2.54 BSC		BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300 BSC		7.62	BSC	
M	0°	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

SOICW-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**



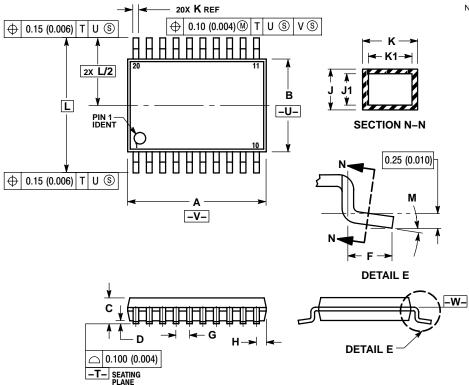
NOTES:

- NOTES:

 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
C	0.23	0.32	
D	12.65	12.95	
Е	7.40	7.60	
е	1.27	BSC	
H	10.05	10.55	
h	0.25	0.75	
٦	0.50	0.90	
θ	0 °	7 °	

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 - SHALL NOT EXCEED 0.15 (0.000) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE SIDE.
 - SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN

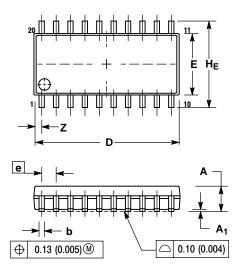
 - FOR REFERENCE ONLY.

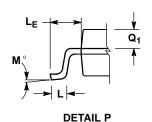
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

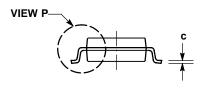
	MILLIMETERS INCHES			HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
M	0°	8°	0°	8°

PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE O**







- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED
- AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z		0.81		0.032

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